

Lecture 24: Memory technology

- Memory landscape
- Volatile memories
- Non-volatile memories

Announcements

- HW2 will be assigned this week end
- There will be a quiz on memory next week

Basic categories of memory

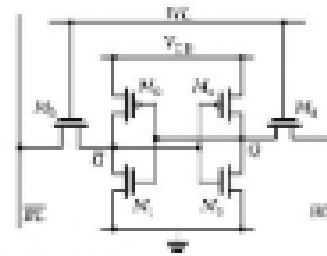
- **Read-Only Memory (ROM)**
 - Can only be read (accessed)
 - Cannot be written (modified)
 - Contents are often set before ROM is placed into the system
- **Random-Access Memory (RAM)**
 - Can be read/written
 - Term used for historical reasons
 - Technically, ROMs are also random access
- **Volatile memory**
 - Lose contents when power is lost
 - Often stores program state, stack, and heap
 - In desktop/server systems, also stores program executable
- **Non-volatile memory**
 - Retain contents when power is lost
 - Used for boot code in almost every system

Memory technologies landscape

| | Volatile | Non-Volatile |
|-----|---|---|
| RAM | Static RAM (SRAM) Dynamic RAM (DRAM) | EEPROM Flash Memory Disk PCM, STTRAM, FeRAM... |
| ROM | n/a | Mask ROM PROM EPROM |

Volatile: Static RAM

- Basic cell
 - Bistable core
 - 4T: uses pullup resistors for M2, M4
 - 6T: uses P-FET for M2, M4
 - Access transistors
 - BL, BL# are provided to improve noise margin
- 6T is typically used (but has poor density)
- Fast access times $O(10\text{ ns})$
- Read/write speeds are symmetric
- Read/write granularity is word



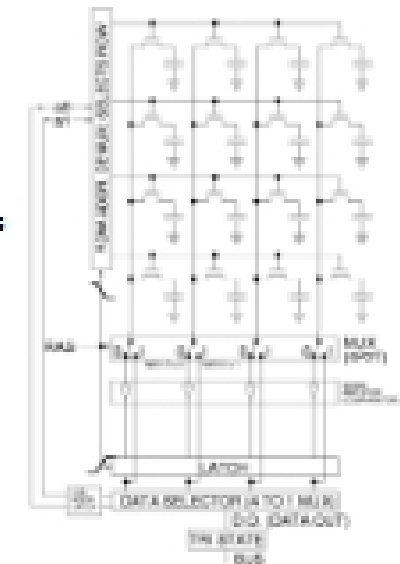
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Volatile: Dynamic RAM

- Requires only 1T and 1C per cell
- Outstanding density, low cost, and cost advantage compared to SRAM
- Small charges involved \rightarrow relatively slow
 - Bit lines must be pre-charged to detect bits
 - Reads are destructive; internal writebacks needed
- Values must be refreshed periodically
 - Prevents charge from leaking away
 - Complicates control circuitry slightly



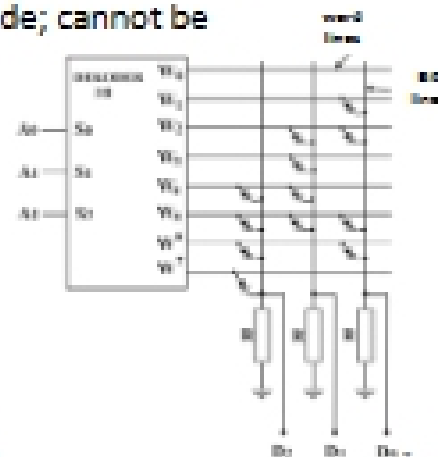
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Non-Volatile: Mask ROM

- The "simplest" memory technology
- Presence/absence of diode at each cell denote value
- Pattern of diodes defined by mask used in fab process
- Contents are fixed when chip is made; cannot be changed
- High upfront setup costs
- Small recurring marginal costs
- Good for applications where
 - Cost sensitivity drives design
 - Upgrading contents not an issue
 - e.g. boot ROM, CPU microcode



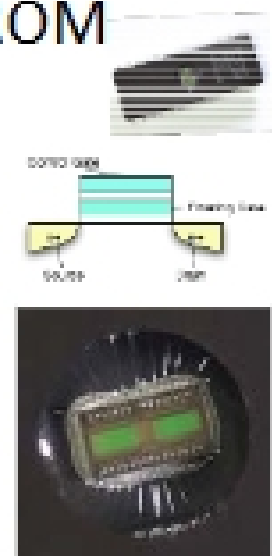
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Non-Volatile: EPROM

- Erasable Programmable Read-Only Memory
- Constructed from floating gate FETs
 - Charge trapped on the FG erases cell
 - High voltage (13V+) applied to the control gate
 - "Writes" the cell with a 0
 - Allows FG charge to be dissipated
- Writing means changing from 1 \rightarrow 0
- Erasing means changing from 0 \rightarrow 1
 - Uses UV light (not electrically!)
 - Erase unit is the whole device
- Retains data for 10-20 years
- Costly because
 - Use of quartz window (UV transparent)
 - Use of ceramic package
- Not used much these days



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Non-Volatile: Flash Storage

- Semiconductor storage
 - 100× – 1000× faster than disk
 - Smaller, lower power, more robust
 - But more \$/GB (between disk and DRAM)

Two types:

- **NOR flash:** bit cell like a NOR gate
 - Random read/write access
 - Used for instruction memory in embedded systems
- **NAND flash:** bit cell like a NAND gate
 - Denser (bits/area), cheaper per GB, but block-at-a-time access
 - Cheaper Used for USB keys, media storage, ...

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Flash Access

- Electrically erasable (like EEPROM, unlike EPROM)
- Erase size is block (not word); *can't do byte modifications*
- Reads are like standard RAM
- Can "write" bits/words (actually, change from 1 → 0)
 - Write cycle is O(microseconds)
 - Slower than RAM but faster than EEPROM
 - To (re)write from 0 → 1, must explicitly erase entire block
 - Erase is time consuming O(milliseconds to seconds)
- Floating gate technology
 - Erase/write cycles are limited (10K to 100K, typically)
 - Flash bits wears out after 1000's of accesses
 - *Wear leveling: remap data to less used blocks*

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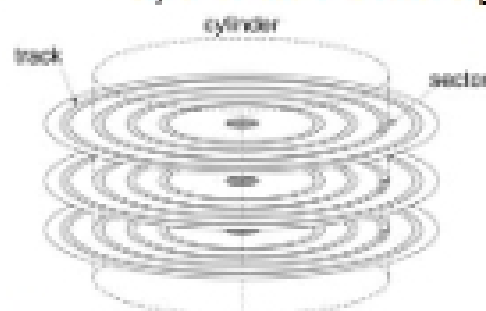
Non-Volatile: Disk Storage

- Rotating magnetic storage



Each sector records

- Sector ID
- Data (512 ~ 4096 bytes)
- Error correcting code (ECC)
 - Hide defects and recording errors
- Synchronization fields and gaps



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Disk Access

- Access to a sector involves
 - Queuing delay if other accesses are pending
 - Seek: move the heads
 - Rotational latency
 - Data transfer
 - Controller overhead
- Manufacturers quote average seek time
 - Based on all possible seeks
 - Locality and OS scheduling lead to smaller actual average seek times
- Smart disk controller allocate physical sectors on disk
 - Present logical sector interface to host
- Disk drives include caches
 - Prefetch sectors in anticipation of access
 - Avoid seek and rotational delay

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